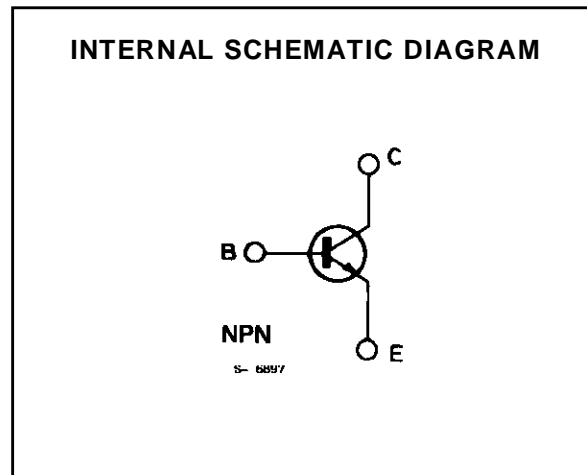
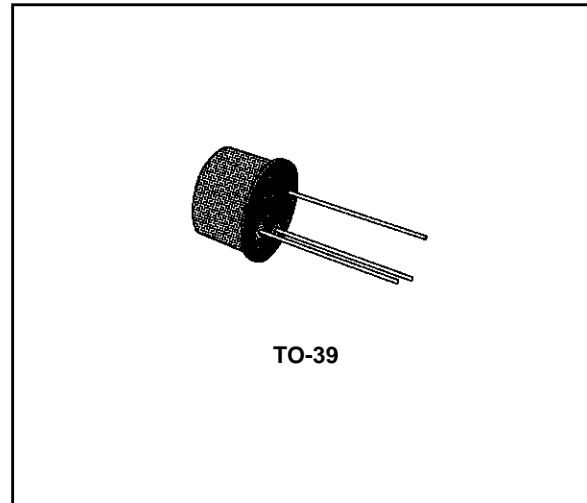


GENERAL PURPOSE AMPLIFIER AND SWITCH

DESCRIPTION

The 2N2102 is a silicon planar epitaxial NPN transistor in Jedec TO-39 metal case. It is intended for a wide variety of small-signal and medium power applications in military and industrial equipments.



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-base Voltage ($I_E = 0$)	120	V
V_{CEO}	Collector-emitter Voltage ($I_B = 0$)	65	V
V_{CER}	Collector-emitter Voltage ($R_{BE} \leq 10 \Omega$)	80	V
V_{EBO}	Emitter-base Voltage ($I_C = 0$)	7	V
I_C	Collector Current	1	A
P_{tot}	Total Power Dissipation at $T_{amb} \leq 25 \text{ }^\circ\text{C}$ at $T_{case} \leq 25 \text{ }^\circ\text{C}$	1	W
		5	W
T_{stg}, T_j	Storage and Junction Temperature	- 65 to 200	$^\circ\text{C}$

THERMAL DATA

$R_{th\ j-case}$	Thermal Resistance Junction-case	Max	35	°C/W
$R_{th\ j-amb}$	Thermal Resistance Junction-ambient	Max	175	°C/W

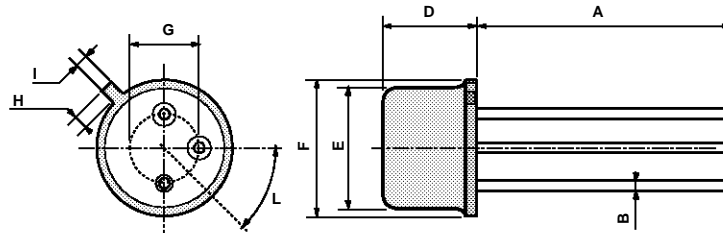
ELECTRICAL CHARACTERISTICS ($T_{amb} = 25\ ^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{CBO}	Collector Cutoff Current ($I_E = 0$)	$V_{CB} = 60\ \text{V}$ $V_{CB} = 60\ \text{V}$ $T_{amb} = 150\ ^\circ\text{C}$			2 2	nA μA
I_{EBO}	Emitter Cutoff Current ($I_C = 0$)	$V_{EB} = 5\ \text{V}$			5	nA
$V_{(BR)\ CBO}$	Collector-base Breakdown Voltage ($I_E = 0$)	$I_C = 100\ \mu\text{A}$	120			V
$V_{CEO(sus)}^*$	Collector-emitter Sustaining Voltage ($I_B = 0$)	$I_C = 30\ \text{mA}$	65			V
$V_{CE(sat)}^*$	Collector-emitter Saturation Voltage	$I_C = 150\ \text{mA}$ $I_B = 15\ \text{mA}$			0.5	V
$V_{BE(sat)}^*$	Base-emitter Saturation Voltage	$I_C = 150\ \text{mA}$ $I_B = 15\ \text{mA}$			1.1	V
h_{FE}^*	DC Current Gain	$I_C = 10\ \mu\text{A}$ $V_{CE} = 10\ \text{V}$ $I_C = 100\ \mu\text{A}$ $V_{CE} = 10\ \text{V}$ $I_C = 10\ \text{mA}$ $V_{CE} = 10\ \text{V}$ $I_C = 150\ \text{mA}$ $V_{CE} = 10\ \text{V}$ $I_C = 500\ \text{mA}$ $V_{CE} = 10\ \text{V}$ $I_C = 1\ \text{A}$ $V_{CE} = 10\ \text{V}$	10 20 35 40 25 10		120	
h_{fe}	High Frequency Current Gain	$I_C = 50\ \text{mA}$ $f = 20\ \text{MHz}$ $V_{CE} = 10\ \text{V}$		6		
NF	Noise Figure	$I_C = 300\ \mu\text{A}$ BW = 1 Hz $V_{CE} = 10\ \text{V}$ $f = 1\ \text{kHz}$ $R_G = 510\ \Omega$			8	dB
C_{CBO}	Collector-base Capacitance	$I_E = 0$ $f = 1\ \text{MHz}$ $V_{CB} = 10\ \text{V}$			15	pF
C_{EBO}	Emitter-base Capacitance	$I_C = 0$ $f = 1\ \text{MHz}$ $V_{EB} = 0.5\ \text{V}$			80	pF

* Pulsed : pulse duration = 300 μs , duty cycle = 1 %.

TO39 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	12.7			0.500		
B			0.49			0.019
D			6.6			0.260
E			8.5			0.334
F			9.4			0.370
G	5.08			0.200		
H			1.2			0.047
I			0.9			0.035
L	45° (typ.)					



P008B

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